



Future Normal in Semiconductor

2025-02-14(금), 10:55-12:40

좌장: 추후업데이트 예정

C. Material Growth & Characterization 분과

[FF2-C] Advanced Devices in Oxide Heterostructures

<p>초청 FF2-C-1 10:55-11:25</p>	<p>Spintronic Security Devices based on Magnetic Random-access Memory Soogil Lee¹, Jaimin Kang², and Byong-Guk Park² ¹Department of Semiconductor Engineering, Gachon University, ²Department of Materials Science and Engineering, KAIST</p>
<p>FF2-C-2 11:25-11:40</p>	<p>Depletion-mode and Enhancement-mode Diamond MOSFETs Simultaneously Fabricated on Heteroepitaxial Diamond Substrates Taemyung Kwak¹, Yoonseok Nam¹, Yeonghwa Kwon¹, Geunho Yoo¹, Seong-woo Kim², and Okhyun Nam² ¹Tech University of Korea, ²Orbray Co., Ltd, Japan</p>
<p>FF2-C-3 11:40-11:55</p>	<p>Monolithic integration of quantum dot light emitting diodes on In_{0.1}Ga_{0.9}As/AIAs distributed Bragg reflectors on Si Tsimafei Laryn^{1,2}, Yeonhwa Kim^{1,3}, Eunkyo Ju^{1,3}, Won Jun Choi¹, and Daehwan Jung¹ ¹Center for Quantum Technology, KIST, ²Division of Nanoscience and Technology, KIST School at University of Science and Technology, ³Department of Materials Science and Engineering, Korea University</p>
<p>FF2-C-4 11:55-12:10</p>	<p>Monolithic Integration of Freestanding Ferroelectric Oxide Membranes for Electrically Tunable Energy Storage Performance Min-Seok Kim¹, Tae Heon Kim¹, Seung-Hyub Baek¹, and Ho Won Jang² ¹KIST, ²Seoul National University</p>
<p>FF2-C-5 12:10-12:25</p>	<p>Wafer-scale single-crystal hexagonal boron nitride integrated hybrid dielectric for two-dimensional transistor arrays Jaewon Wang¹, Hyeonwoo Lee¹, Haeng Un Yeo¹, Cheol Hwan Yoon¹, Junseop Noh¹, Kitae Park¹, Joonki Suh¹, Tae-Sik Yoon¹, Changwook Jeong¹, Soon-Yong Kwon¹, Jaemin Kim^{1,2}, Hyung-Joon Shin^{1,2}, Zonghoon Lee^{1,2}, Min Seok Yoo³, Minsu Seol³, and Chanyong Hwang⁴ ¹UNIST, ²CMCM, IBS, ³2D Device Laboratory, Samsung Advanced Institute of Technology, ⁴Quantum Technology Institute, KRISS</p>



제 32회 한국반도체학술대회

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<p>FF2-C-6 12:25-12:40</p>	<p>High-performance Flash Memory with 1T-MoS₂ Floating Gate Hyelim Shin¹, Gunhoo Woo², and Taesung Kim^{1,2,3} ¹School of Semiconductor Convergence Engineering, Sungkyunkwan University, ²SKKU Advanced Institute of Nanotechnology, Sungkyunkwan University, ³School of Mechanical Engineering, Sungkyunkwan University</p>
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